

Method for improving endurance and breakdown characteristics of metal/ferroelectric/metal capacitor by modulating deposition cycle ratio

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Abstract: Hafnium-based ferroelectric devices show great potential in the application of high-efficiency memory technology. In this work, we study the effect of modulating deposition cycle ratio on memory windows and endurance of metal/ferroelectric/metal (MFM) capacitors. We fabricated capacitors with 3 conditions for $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ thin film of the deposition cycle ratio are 1:1, 5:5, 10:10, respectively. All samples have nearly the same memory window and the devices with a 10:10 cycle ratio could tolerate more bipolar cycles. By comparing the leakage and breakdown characteristics, the improved endurance for the 10:10 device is due to the lower trap density of oxygen vacancy. Furthermore, the deposition cycle ratio can be further optimized to make the trade-off between the performance and reliability in the ferroelectric devices.

Key words: CMOS technology; Hafnium-based ferroelectric; Endurance; Breakdown; Cycle ratio

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1. Introduction

Memory technology is driven by the prosperity of a data-based economy and higher performance and efficiency are required [1]. The ferroelectric field-effect transistor (FeFET) or the ferroelectric tunneling junction (FTJ) takes advantage of the non-destructive read operation and promise improved scalability of the memory cell compared to mature capacitor-based ferroelectric random access memory (FeRAM), and all kinds of devices attract great research attention since the discovery of ferroelectricity in doped- HfO_2 thin films [2-4]. Hafnium-based ferroelectric devices show great potential for high-density, high-performance, and low-power applications, due to their fast switching property, good scalability, and CMOS compatibility. However, limited endurance is a bottleneck for Hafnium-based memory devices [5, 6].

The endurance represents the ferroelectric material to withstand a certain number of pulse cycles. The alternative positive and negative electric field is applied to ferroelectric thin film during endurance measurement. Due to material degradation, the

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remnant polarization of the device is reduced. Before the remnant polarization completely reduces to zero, the device always experiences a hard breakdown and becomes leaky, and loses its memory function. The oxygen vacancy trap generation and movement are demonstrated as the main cause for endurance degradation [6]. First, the oxygen vacancy traps are generated at the interface between the ferroelectric layer and the metal electrode. Second, the oxygen vacancy traps move into ferroelectric bulk under an alternating electric field. Meanwhile, the charged traps will induce ferroelectric domain pinning and remnant polarization reduction. Finally, by further applying an alternating electric field, oxygen vacancy traps are continuously generated and gradually form a leakage path. Therefore, the percolation conduction path connection the electrodes and leads to a hard breakdown of the ferroelectric layer.

Based on the above endurance degradation mechanism, methods for improving endurance include suppressing trap generation at the interface, preventing the movement of traps in the bulk ferroelectric layer, and hindering the formation of the percolation path. There are many types of research on suppressing trap generation, such as interface passivation and annealing [7-10]. Recently, there are several works is proposed on preventing trap movement and percolation path formation. Recently, it is reported that endurance is improved by inserting a dielectric layer into the ferroelectric layer, the improvement of endurance is explained by grain boundary interruption [13]. However, the insertion of a paraelectric layer is detrimental to performance. Furthermore, the modulation of deposition cycle ratio has been proposed in the aluminum scandium nitride (AlScN) ferroelectric film to improve the dielectric breakdown characteristic [14]. The breakdown suppression mechanism is the deflection effect of percolation path formation at the multilayer interfaces or a retarded effect in the more compressive layers of the multilayer structure. Though the deposition cycle ratio effect of Si-doped HfO_2 [11] and $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ [12] ferroelectric device has been studied, however, the mechanism for endurance difference is not clear.

In this work, we study the effects of the deposition cycle ratio of $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ ferroelectric film on the performance and reliability of metal/ferroelectric/metal (MFM) capacitors. The memory window and endurance characteristic are evaluated by triangle pulse and square pulse cycling, respectively. The oxygen vacancy behavior during endurance is analyzed by direct current (DC) TDDB and leakage measurement. At last, the mechanism is explained from the oxygen vacancy generation and the influence on performance and reliability are discussed.

2. Experimental methods

The device structure is illustrated in Fig. 1. The devices were fabricated on a p-type Si substrate. After cleaning by diluted buffer oxide etch (dBOE), TiN (20 nm) was deposited on Si for backside electrical contact by PVD. Then different cycle ratios of atomic layer deposition (ALD) $\text{Hf}_{0.5}\text{Zr}_{0.5}\text{O}_2$ layer are deposited as ferroelectric layer grown by ALD at 300 °C using tetrakis-(ethylmethylamino)-hafnium (TEMA-Hf) as Hf precursor, tetrakis-(ethylmethylamino)-zirconium (TEMA-Zr) as Zr precursor, and H_2O as O source. Then top electrode TiN (10 nm) by CVD and W (75 nm) by ALD are

deposited, respectively. Finally, all devices were annealed at 550 °C for 30 s in N₂ atmosphere to crystallize the Hf_{0.5}Zr_{0.5}O₂ layer, and capacitors were lithographically formed. The total thickness is chosen as 10 nm, due to better ferroelectricity[7, 15].

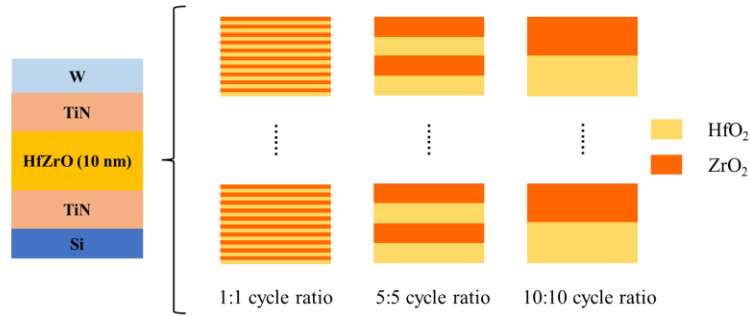


Fig. 1. Schematic of the device structure of MFM capacitor with different deposition cycle ratios.

Electrical Measurements are done by TFAalyzer 3000 (for room temperature test) and Agilent 4156C (for elevated temperature test). Dynamic hysteresis measurement with triangle pulse is used for the remnant polarization measurement. Fatigue measurement with the square pulse is used for wake-up and endurance measurement. Dynamic hysteresis measurement with the square pulse of different pulse widths ranging from 1 s to 100 s is used to replace the conventional TDDB measurement for ease of comparison of endurance. Leakage measurement with 500 ms voltage step duration is used to characterize the leakage evolving during endurance or TDDB. All capacitors are measured after 1000 cycles of wake-up. For the reason to avoid the parasitic effects due to series resistance, the endurance measurement is done at 10 kHz, and dynamic hysteresis measurement is done at 1 kHz.

3. Results and discussions

3.1. Device performance and reliability

Fig. 2 shows the I - V and P - V characteristics of MFM capacitors with different deposition cycle ratios. The triangle pulse with 3 V amplitude and 1 kHz are applied. The amplitude of 3 V is chosen to ensure the saturated spontaneous polarization is reached because the current peak is almost disappeared at about 2.75 V as shown in Fig. 2. The extracted ferroelectric properties are summarized in Table 1. For more robust results, the above parameters are extracted from more than 30 devices for each sample. The permittivity is extracted from the linear region of the P - V curve. Then, the spontaneous polarization P_s - V could be obtained by subtraction of background polarization from total polarization. The remnant polarization (P_r) and the saturated polarization (P_{ss}) are corresponding to the polarization charge difference where applied voltage equals 0 and $\pm 3V$, respectively. The coercive voltage (V_c) is the corresponding applied voltage where P equals 0. As summarized in Table 1, the P_r and P_{ss} are almost the same for all samples, though the value of the 5:5 sample is slightly higher. As the

deposition cycle ratio increases, the permittivity increases, and V_c decreases. Based on the above results, it is concluded that all samples are a mixture of ferroelectric (orthorhombic) and non-ferroelectric (monoclinic and tetragonal) phases. As the deposition cycle ratio increases, the ferroelectric phase shows little change, and the non-ferroelectric phase has changed from monoclinic to tetragonal. Thus, the memory window defined by $2P_r$ is nearly the same for all samples. Considering the initial $P-V$ shows pinched hysteresis loop (not shown), thus the extracted parameters of all samples are compared after 1000 cycles wake-up conditions.

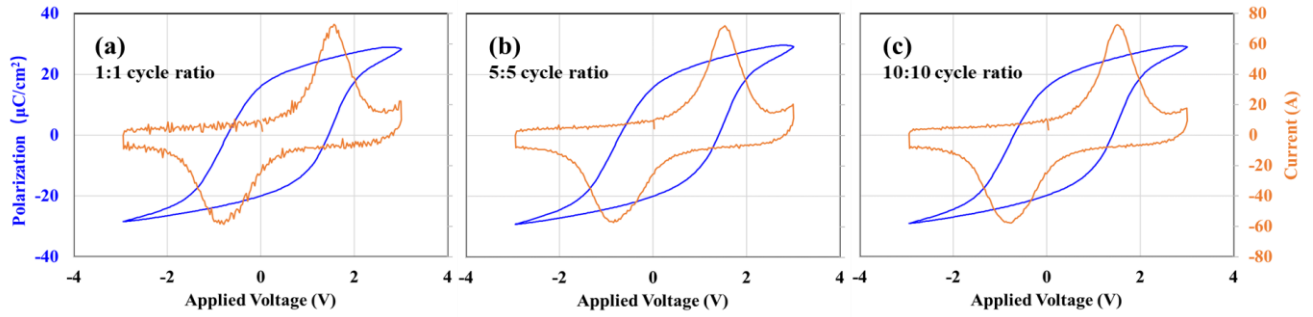


Fig. 2. $I-V$ and $P-V$ characteristics of MFM capacitors with different deposition cycle ratios.

Table 1. Physical parameters for different deposition cycle ratios.

Parameters	deposition cycle ratio		
	1:1	5:5	10:10
$2P_r$ ($\mu\text{C}/\text{cm}^2$)	35.84 ± 0.29	36.35 ± 0.22	35.97 ± 0.43
$2P_{ss}$ ($\mu\text{C}/\text{cm}^2$)	39.78 ± 0.44	40.47 ± 0.23	39.84 ± 0.45
$2V_c$ (V)	2.17 ± 0.02	2.13 ± 0.01	2.11 ± 0.01
permittivity	31.49 ± 0.36	33.43 ± 0.56	34.48 ± 0.32
$I_{\text{leak}@3 \text{ MV/cm}}$ (A/cm^2)	2.78×10^{-2}	2.51×10^{-2}	2.08×10^{-2}
V_{BD} (V)	3.56	3.49	3.54
V_c / V_{BD}	0.304	0.305	0.298

The endurance characteristic is compared. The bipolar square pulse with an amplitude of 3 V and frequency of 10 kHz is applied. In Fig. 3(a), it is shown that a set of representative endurance results. The memory window keeps nearly constant until 10^4 cycles. After 10^4 cycles, the memory window starts to collapse. Then, the capacitor breakdown before the memory window completely disappears. The breakdown leads to a great leakage increment, and the measured P_r values show a sudden jump. The endurance is also a random process as other reliability issues. The endurance cycles are statistically shown in Fig. 3(b), the average endurance cycles are 1.13×10^5 , 0.78×10^5 , 1.55×10^5 for deposition cycle ratios of 1:1, 5:5, 10:10, respectively. The endurance difference will discuss later.

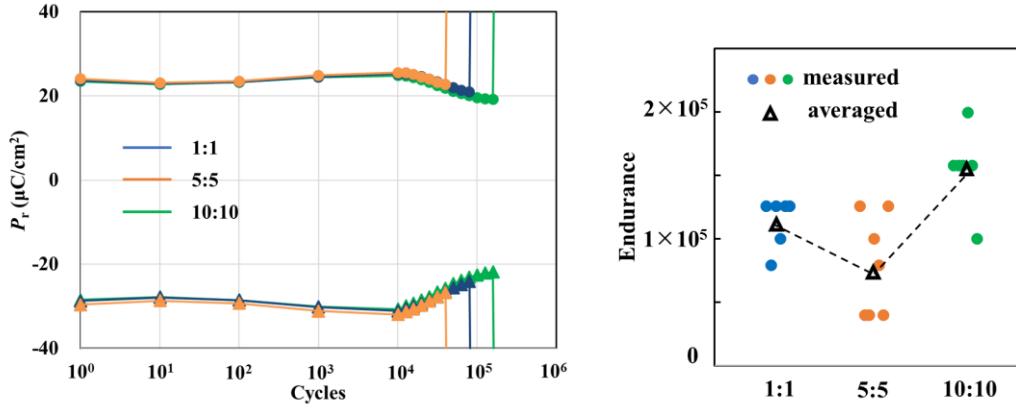


Fig. 3. The endurance characteristic. (a) The remnant polarization evolution during bipolar pulse cycling. (b) The statistic distribution of endurance cycles.

3.2. Trap density of oxygen vacancy

Considering the endurance mechanism is domain pinning induced by the oxygen vacancy[6], the leakage and breakdown measurements are also applied to verify the trap generation. Fig. 4 compares the leakage current and time-zero breakdown (TZDB) characteristic. The forward DC linear voltage sweep is applied to measure the leakage current and breakdown voltage. The leakage current and breakdown voltage are extracted and listed in Table 1. The 10:10 deposition cycle ratio samples get the lowest leakage current, and the 1:1 deposition cycle ratio samples get the highest breakdown voltage.

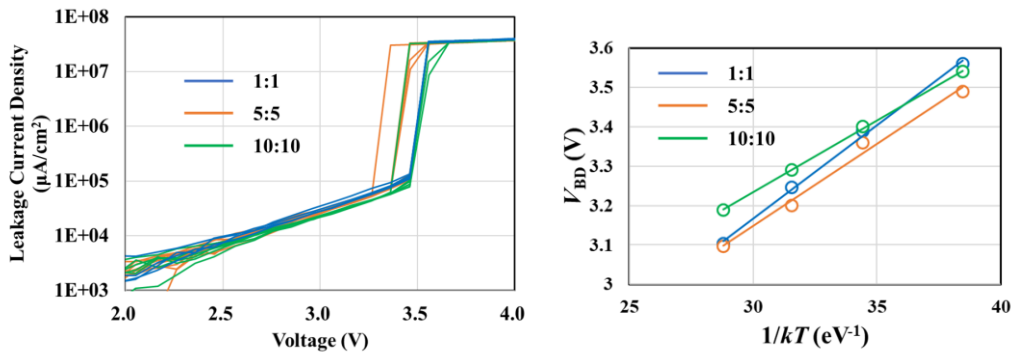


Fig. 4. The leakage and TZDB characteristics of MFM capacitors. (a) leakage current density vs. applied voltage. (b) V_{BD} vs. $1/kT$.

The leakage mechanism is mainly due to oxygen vacancy trap-assistant tunneling at grain boundary[6]. As summarized in Table 1, as the deposition cycle ratio decreases, the leakage current increases, suggesting a higher oxygen vacancy density. The temperature dependence of V_{BD} could be fitted by thermal activation relation. The extracted thermal activation energy is 0.0473, 0.0417, 0.0365 eV for 1:1, 5:5, 10:10 sample, respectively.

For further confirmation of the cycle ratio dependence of the breakdown characteristic, the DC time-dependent dielectric breakdown (TDDB) characteristic is

compared. For convenient comparison of endurance, the measurement is done by dynamic hysteresis measurement with the square pulse of different pulse widths ranging from 1 s to 100 s to replace the conventional TDDB measurement. The minimum time resolution is 25 ms. The applied stress voltage is 3.4 V. The Weibull distribution of time to breakdown (t_{BD}) is shown in Fig. 5. The 63% failure times (t_{63}) is 2.79 s, 1.17 s, 2.31 s, and the Weibull slopes are 0.74, 1.66, 1.60 for 1:1, 5:5, 10:10 cycle ratio samples, respectively.

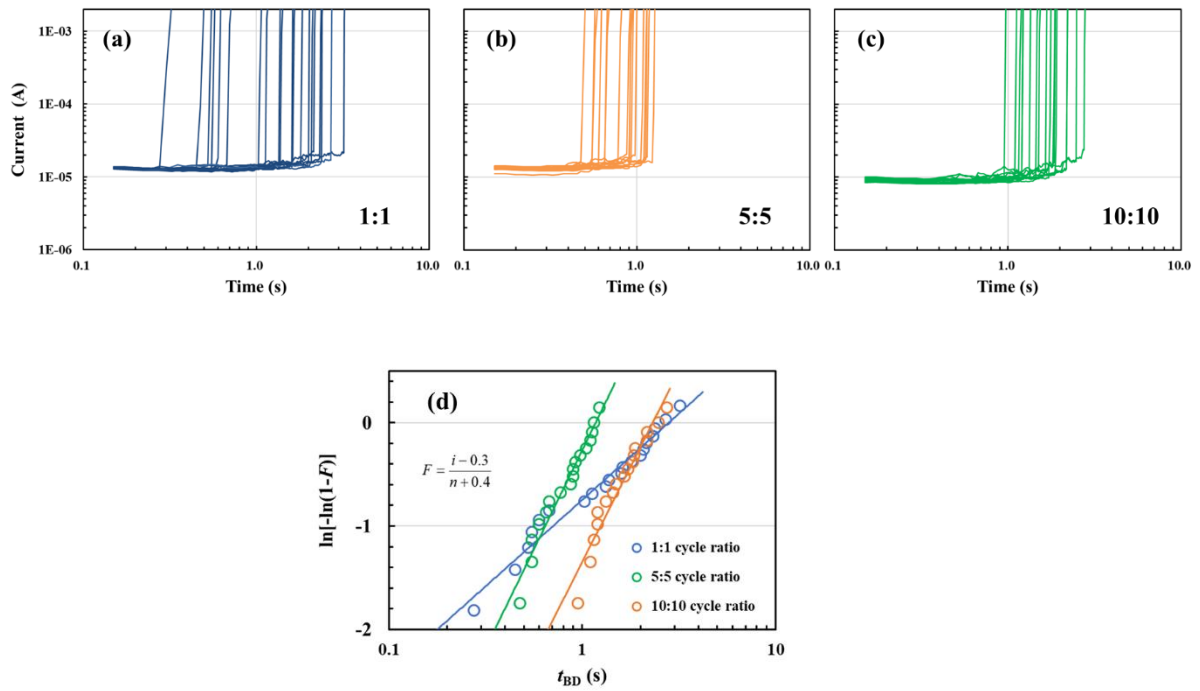


Fig. 5. The TDDB characteristic. (a-c) The current-duration curve for 1:1, 5:5, 10:10 deposition cycle ratio. (d) The Weibull distribution of time to breakdown.

The tendency of t_{63} is consistent with TZDB results, however, a different Weibull slope for the 1:1 cycle ratio sample is observed. The Weibull slope represents the shape factor of the Weibull distribution, and it is influenced by the thickness of the dielectric, size of trapping cell, and time-exponent of the trap generation rate. The Weibull slope reduction could be explained by time-exponent decreasing, induced by a slower trap generation process. Though slightly larger t_{63} is obtained for the 1:1 cycle ratio sample, the broad distribution is detrimental to device reliability. Furthermore, the TDDB distributions of 5:5 and 10:10 cycle ratios have almost the same Weibull slope which suggests the same trap generation mechanism. The larger t_{63} for the 10:10 cycle ratio sample could be explained by reducing oxygen vacancy density.

3.3. Discussions on the trade-off between memory window and endurance

For further design optimization of ferroelectric devices, there are 2 points to be addressed by modulating the deposition cycle ratio. First, high endurance is obtained

for a high deposition cycle ratio due to the reduction of the trap density of oxygen vacancy. In our experiment, oxygen density is the most critical origin for device fatigue. It shows that as increasing the deposition cycle ratio, the oxygen trap density could be suppressed. In our experiment, the thickest deposition layer is about 0.75 nm (for 10:10 cycle ratio), which could be interface-determined. The possible origin of traps could be the interface trap between each deposition layer. It makes an interface-determined trap density. Further increasing the deposition cycle ratio may lead to a transition from interface-determined to bulk-determined. Second, the memory window would be reduced by changing the deposition cycle ratio. In our experiment, when the thickness of each deposition layer is less than 1 nm, the memory window shows little change. However, when further increase the deposition cycle ratio, more non-ferroelectric phases will form and the memory window reduces, as shown in ref [12].

4. Conclusion

We study the effects of modulation deposition cycle ratio on performance and reliability of Hf-based ferroelectric devices, the results show a potential method with unchanged memory window and enhanced endurance in MFM capacitor. On the one hand, with different deposition cycle ratios of 1:1, 5:5, and 10:10, the memory window shows little difference. On the other hand, the highest endurance cycles are obtained for the device with a 10:10 cycle ratio. The trap density and generation process of oxygen vacancy plays important role in these samples. It provides a guideline for ferroelectric device optimization by modulating the deposition cycle ratio.



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